

R1LV1616R Series

16Mb Advanced LPSRAM (1M wordx16bit / 2M wordx8bit)

REJ03C0101-0400Z Rev.4.00 2007.09.12

Description

The R1LV1616R Series is a family of low voltage 16-Mbit static RAMs organized as 1048576-words by 16-bit, fabricated by Renesas's high-performance 0.15um CMOS and TFT technologies.

The R1LV1616R Series is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives.

The R1LV1616R Series is packaged in a 52pin micro thin small outline mount device[μ TSOP / 10.79mm x 10.49mm with the pin-pitch of 0.4mm], a 48pin thin small outline mount device[TSOP / 12mm x 20mm with the pin-pitch of 0.5mm] or a 48balls fine pitch ball grid array [f-BGA / 7.5mmx8.5mm with the ball-pitch of 0.75mm and 6x8 array] . It gives the best solution for a compaction of mounting area as well as flexibility of wiring pattern of printed circuit boards.

Features

- Single 2.7-3.6V power supply
- Small stand-by current:2µA (3.0V, typ.)
- Data retention supply voltage =2.0V
- No clocks, No refresh
- · All inputs and outputs are TTL compatible
- Easy memory expansion by CS1#, CS2, LB# and UB#
- Common Data I/O
- Three-state outputs: OR-tie capability
- OE# prevents data contention on the I/O bus
- Process technology: 0.15um CMOS



Ordering Information

Type No.	Access time	Package
R1LV1616RSD-5S%	55 ns (Note0)	
R1LV1616RSD-7S%	70 ns	350-mil 52-pin plastic μ - TSOP(II) (normal-bend type) (52PTG)
R1LV1616RSD-8S%	85 ns	(1.5.1.6. 35.1.6. 7)
R1LV1616RBG-5S%	55 ns (Note0)	
R1LV1616RBG-7S%	70 ns	7.5mmx8.5mm f-BGA 0.75mm pitch 48ball
R1LV1616RBG-8S%	85 ns	
R1LV1616RSA-5S%	55 ns (Note0)	
R1LV1616RSA-7S%	70 ns	12mm x 20mm plastic TSOP(I) (normal-bend type) (48P3R)
R1LV1616RSA-8S%	85 ns	(a a a a a gray (a a a a gray)

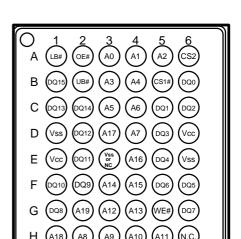
Note0. 55ns parts can be supported under the condition of the input timing limitation toward SRAM on customer's system. Please contact our sales office in your region, in case of the inquiry for 55ns parts.

% - Temperature version; see table below

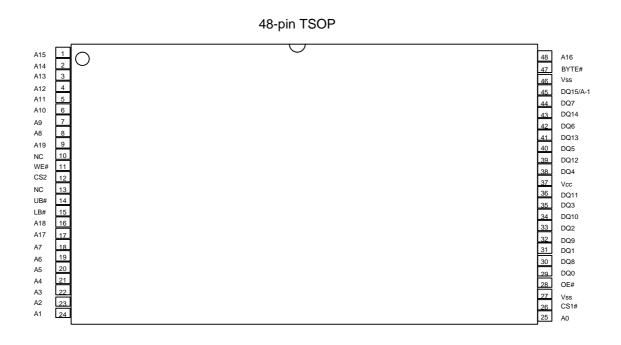
%	Temperature Range
R	0 ~ +70 °C
I	-40 ~ +85 °C

Pin Arrangement

52-pin µTSOP A15 A16 \bigcirc A14 BYTE# A13 UB# A12 Vss A11 LB# A10 DQ15/A-1 A9 A8 DQ7 DQ14 9 10 11 A19 CS1# DQ6 DQ13 WE# DQ5 DQ12 NC DQ4 Vcc NC CS2 DQ11 NC DQ3 NC DQ10 A18 DQ2 A17 A6 A5 A4 A3 A2 DQ9 DQ1 DQ8 DQ0 OE# Vss NC A0

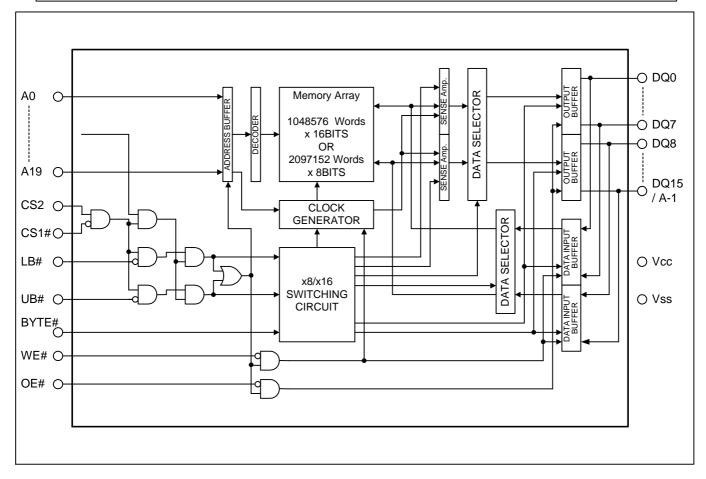


48-pin fBGA



Pin Description						
Pin name	Function					
A0 to A19	Address input					
DQ 0 to DQ15	Data input/output					
CS1# &CS2	Chip select					
WE#	Write enable					
OE#	Output enable					
LB#	Lower byte select					
UB#	Upper byte select					
Vcc	Power supply					
Vss	Ground					
BYTE#	Byte (x8 mode) enable input					
NC	Non connection					

Block Diagram



Note. BYTE# pin supported by only TSOP and uTSOP types.



Operating Table

CS1#	CS2	BYTE#	LB#	UB#	WE#	OE#	DQ0-7	DQ8-14	DQ15	Operation
Н	Х	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	Stand by
Х	L	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	Stand by
Х	Х	Н	Н	Н	Х	Х	High-Z	High-Z	High-Z	Stand by
L	Н	Н	L	Н	L	Х	Din	High-Z	High-Z	Write in lower byte
L	Н	Н	L	Н	Н	L	Dout	High-Z	High-Z	Read from lower byte
L	Н	X	Х	Х	Н	Н	High-Z	High-Z	High-Z	Output disable
L	Н	Н	Н	L	L	Х	High-Z	Din	Din	Write in upper byte
L	Н	Н	Н	L	Н	L	High-Z	Dout	Dout	Read from upper byte
L	Н	Н	L	L	L	Х	Din	Din	Din	Write
L	Н	Н	L	L	Н	L	Dout	Dout	Dout	Read
L	Н	L	L	L	L	Х	Din	High-Z	A-1	Write
L	Н	L	L	L	Н	L	Dout	High-Z	A-1	Read

Note 1. H:VIH L:VIL X: VIH or VIL

Absolute Maximum Ratings

Parameter	Parameter Symbol Val			Unit
Power supply voltage relative to Vss	Vcc		-0.5 to +4.6	V
Terminal voltage on any pin relation toVss	VT	-0	.5*1 to Vcc+0.3*2	V
Power dissipation	Рт		0.7	W
	Tons	R ver.	0 to +70	°C
Operation temperature	Topr	I ver.	-40 to +85	°C
Storage temperature	Tstg	-65 to +150		°C
Character to an author was an are to down him	Thing	R ver.	0 to +70	°C
Storage temperature range under bias	Tbias	I ver.	-40 to +85	°C

Note 1. -2.0V in case of AC (Pulse width \leq 30ns)



^{2.} BYTE# pin supported by only TSOP and uTSOP types. When apply BYTE# ="L", please assign LB#=UB#="L".

^{2.} Maximum voltage is +4.6V

Recommended Operating Conditions

Parameter	Symbol	Min.	Тур.	Max.	Unit	Note	
Cupply voltage	Vcc	2.7	3.0	3.6	V		
Supply voltage		Vss	0	0	0	V	
Input high voltage	Input high voltage		2.4	-	Vcc+0.2	V	
Input low voltage		VIL	-0.2	-	0.4	V	1
Ambient temperature range	R ver.	- C	0	-	+70	°C	2
Ambient temperature range	I ver.	Та	-40	-	+85	°C	2

Note 1. -2.0V in case of AC (Pulse width ≤ 30 ns)

DC Characteristics

Parameter	Symbol	Min.	Typ.*1	Max.	Unit	Test conditions*2		
Input leakage current	Iu	-	-	1	μΑ	Vin=Vss to Vcc		
Output leakage current	ILo	ı	ı	1	μΑ	CS1# =VIH or CS2=VIL or OE# = VIH or WE# =VIL or LB# =UB# =VIH,VI/O=Vss to Vcc		
Average energting	Icc ₁	-	25	40	mA	Min. cycle, duty =100% I I/O = 0 mA, CS1# =VIL, CS2=VIH Others = VIH / VIL		
Average operating current	lcc2	-	2	5	mA	Cycle time = 1 μ s, I I/O = 0 mA, CS1# \leq 0.2V, CS2 \geq Vcc-0.2V VIH \geq Vcc-0.2V , VIL \leq 0.2V, duty=100%		
Standby current	Isb	-	0.1	0.3	mA	CS2=VIL		
		-	2	6	μA	~+25°C V in ≥ 0V (1) 0V≤CS2≤0.2V or		
Standby current	Is _{B1}	-	4	12	μΑ	~+40°C (2) CS2≥Vcc-0.2V, CS1# ≥Vcc-0.2V or		
Standby current	ISB1	-		25	μA	~+70°C (3)LB# =UB# ≥Vcc-0.2V, CS2≥Vcc-0.2V,		
		-	-	40	μΑ	CS1# ≤0.2V ~+85°C Average value		
Output hige voltage	Vон	2.4	-	-	V	lон = -1mA		
Output Low voltage	Vol	-	-	0.4	V	IoL = 2mA		

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= 25°C), and not 100% tested.



^{2.} Ambient temperature range depends on R/I-version. Please see table on page 2.

^{2.} BYTE# pin supported by only TSOP and uTSOP types. BYTE# ≥ Vcc-0.2V or BYTE# ≤ 0.2V

Capacitance

 $(Ta = +25^{\circ}C, f = 1MHz)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions	Note
Input capacitance	C in	-	-	10	pF	V in = 0V	1
Input / output capacitance	C 1/O	-	-	10	pF	V I/O = 0V	1

Note 1:This parameter is sampled and not 100% tested.

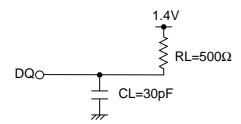
AC Characteristics

Test Conditions (Vcc= $2.7 \sim 3.6$ V, Ta = $0 \sim +70$ °C / $-40 \sim +85$ °C *)

• Input pulse levels: VIL= 0.4V,VIH=2.4V

• Input rise and fall time: 5ns

Input and output timing reference levels: 1.4VOutput load: See figures (Including scope and jig)



Note: Temperature range depends on R/I-version. Please see table on page 2.



Read Cycle

Parameter	Symbol	R1LV1616R**- 5S (Note0)			616R**- 'S		616R**- 3S	Unit	Notes
	-	Min.	Max.	Min.	Max.	Min.	Max.		
Read cycle time	t RC	55	1	70	-	85	-	ns	
Address access time	t AA	-	70	1	70	1	85	ns	
Chin pologt access time	t _{ACS1}	-	55	1	70	1	85	ns	
Chip select access time	t _{ACS2}	-	55	-	70	-	85	ns	
Output enable to output valid	t oe	-	35	-	35	-	45	ns	
Output hold from address change	tон	10	-	10	-	10	-	ns	
LB#,UB# access time	t BA	-	55	-	70	-	85	ns	
Chip select to output in low-Z	t clz	10	-	10	-	10	-	ns	2,3
LB#,UB# enable to low-Z	t BLZ	5	-	5	-	5	-	ns	2,3
Output enable to output in low-Z	t olz	5	-	5	-	5	-	ns	2,3
Chin decelerate systematic high 7	t CHZ1	0	20	0	25	0	30	ns	1,2,3
Chip deselect to output in high-Z	t CHZ2	0	20	0	25	0	30	ns	1,2,3
LB#,UB# disable to high-Z	t BHZ	0	20	0	25	0	30	ns	1,2,3
Output disable to output in high-Z	t onz	0	20	0	25	0	30	ns	1,2,3



Write Cycle

Parameter	Symbol	R1LV1616R**- 5S (Note0)			R1LV1616R**- 7S		616R**- S	Unit	Notes
		Min.	Max.	Min.	Max.	Min.	Max.		
Write cycle time	t wc	55	-	70	-	85	-	ns	
Address valid to end of write	t aw	50	-	65	ı	70	ı	ns	
Chip selection to end of write	tcw	55	-	65	-	70	-	ns	5
Write pulse width	t wp	40	-	55	-	60	-	ns	4
LB#,UB# valid to end of write	t _{BW}	50	-	65	-	70	-	ns	
Address setup time	t AS	0	-	0	-	0	-	ns	6
Write recovery time	t wr	0	-	0	-	0	-	ns	7
Data to write time overlap	tow	25	-	35	-	40	-	ns	
Data hold from write time	t DH	0	-	0	-	0	-	ns	
Output active from end of write	tow	5	-	5	-	5	-	ns	2
Output disable to output in high-Z	t onz	0	20	0	25	0	30	ns	1,2
Write to output in high-Z	t wHz	0	20	0	25	0	30	ns	1,2

Note0. 55ns parts can be supported under the condition of the input timing limitation toward SRAM on customer's system. Please contact our sales office in your region, in case of the inquiry for 55ns parts. In case of tAA =70ns, tRC =70ns.

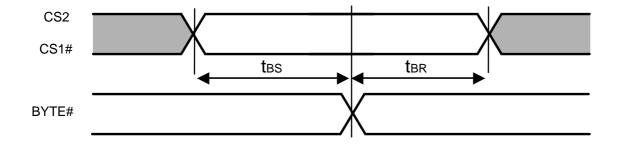
- 1. tchz, tohz, twhz and tbhz are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
- 2. This parameter is sampled and not 100% tested.
- 3. AT any given temperature and voltage condition, thz max is less than tLz min both for a given device and form device to device.
- 4. A write occurs during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#. A write begins at the latest transition among CS1# going low, CS2 going high, WE# going low and LB# going low or UB# going low.
 - A write ends at the earliest transition among CS1# going high, CS2 going low, WE# going high and LB# going high or UB# going high. twp is measured from the beginning of write to the end of write.
- 5. tcw is measured from the later of CS1# going low or CS2 going high to end of write.
- 6. tas is measured the address valid to the beginning of write.
- 7. twn is measured from the earliest of CS1# or WE# going high or CS2 going low to the end of write cycle.



Byte enable (supported by only 48-pin TSOP and 52-pin μ TSOP)

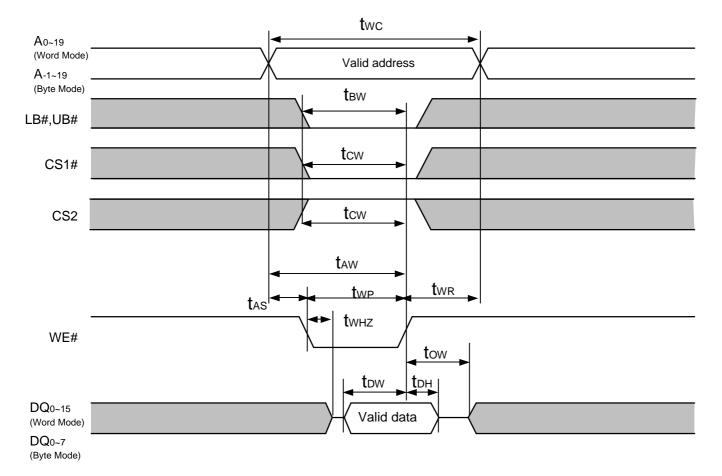
Doromotor	Cumbal	R1LV1616R**-5S		R1LV161	6R**-7S	R1LV16	16R**-8S	Unit	Notes
Parameter	Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Offic	Notes
Byte setup time	t BS	5	1	5	1	5	-	ms	
Byte recovery time	t BR	5	-	5	-	5	-	ms	

BYTE# Timing Waveform

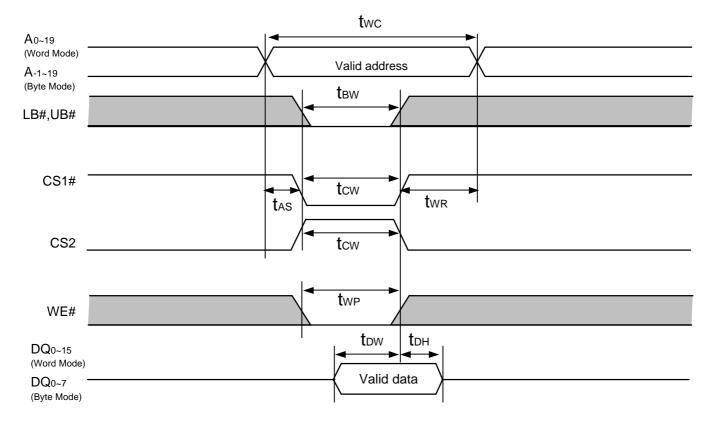


Timing Waveform Read Cycle **t**RC A0~19 (Word Mode) Valid address A-1~19 **t**AA tон (Byte Mode) t_{BA} LB#,UB# **t**BHZ t_{ACS1} CS1# t_{CHZ1} $t_{\hbox{ACS2}}$ CS2 t_{CHZ2} **t**oE OE# tolz toHZWE# = "H" level DQ0~15 (Word Mode) **t**BLZ Valid data DQ0~7 (Byte Mode)

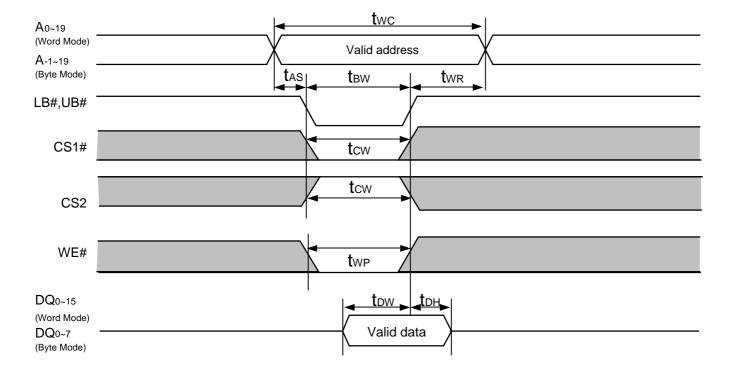
Write Cycle (1) (WE# Clock)



Write Cycle (2) (CS1#, CS2 Clock, OE#=VIH)



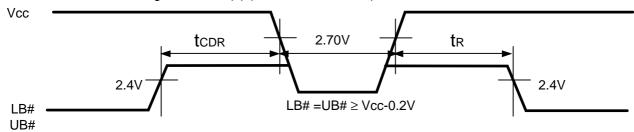
Write Cycle (3) (LB#,UB# Clock, OE#=VIH)



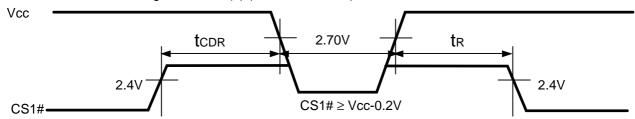
Data Retention Characteristics									
Parameter	Symbol	Mln.	Typ.*1	Max.	Unit	Test conditions*2,3			
Vcc for data retention	Vdr	2.0	-	3.6	V	V in ≥ 0V (1) $0V \le CS2 \le 0.2V$ or (2) $CS2 \ge Vcc-0.2V$, $CS1# \ge Vcc-0.2V$ or (3) $LB# = UB# \ge Vcc-0.2V$, $CS2 \ge Vcc-0.2V$, $CS1# \le 0.2V$			
		-	2	6	μA	~+25°C	Vcc=3.0V,Vin≥0V (1) 0V ≤ CS2 ≤ 0.2V or		
Data retention current		-	4	12	μA	~+40°C	(2) CS2 ≥ Vcc-0.2V, CS1# ≥ Vcc-0.2V or		
Data retention current	ICC DR	-	-	25	μA	~+70°C	(3) LB# =UB# ≥Vcc-0.2V, CS2 ≥ Vcc-0.2V, CS1# ≤ 0.2V		
		-	-	40	μΑ	~+85°C	Average value		
Chip deselect to data retention time	tcdr	0	-		ns				
Operation recovery time	t R	5	-	-	ms	See n	etention waveform		

- Note 1. Typical parameter of ICCDR indicates the value for the center of distribution at Vcc=3.0V and not 100% tested.
 - 2. BYTE# pin supported only by TSOP and uTSOP types. BYTE# ≥ Vcc-0.2V or BYTE# ≤ 0.2V
 - 3. Also CS2 controls address buffer, WE# buffer ,CS1# buffer ,OE# buffer ,LB# ,UB# buffer and Din buffer .If CS2 controls data retention mode,Vin levels (address, WE# ,OE#,CS1#,LB#,UB#,I/O) can be in the high impedance state. If CS1# controls data retention mode, CS2 must be CS2 ≥ Vcc-0.2V or 0V ≤ CS2 ≤ 0.2V. The other input levels (address, WE# ,OE#,CS1#,LB#,UB#,I/O) can be in the high impedance state.

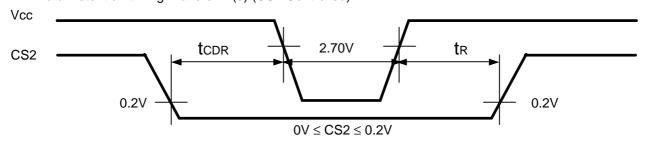
Data Retention timing Waveform (1) (LB#,UB# Controlled)



Data Retention timing Waveform (2) (CS1# Controlled)



Data Retention timing Waveform (3) (CS2 Controlled)





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Old Company Name in Catalogs and Other Documents

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April 1st, 2010 Renesas Electronics Corporation

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